



### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Features**

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 3kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Mechanical Data**

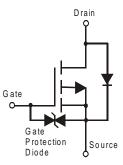
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



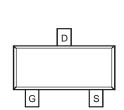


SOT23









Top View

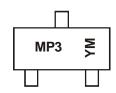
## **Ordering Information** (Note 5)

| Part Number | Compliance | Case  | Packaging                |
|-------------|------------|-------|--------------------------|
| DMP2035U-7  | Standard   | SOT23 | 3,000 / 7" Tape & Reel   |
| DMP2035UQ-7 | Automotive | SOT23 | 3,000 / 7" Tape & Reel   |
| DMP2035U-13 | Standard   | SOT23 | 10,000 / 13" Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



MP3 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{\gamma}$  = Year (ex: D = 2017) M = Month (ex: 9 = September)

Date Code Key

| Year  | 2009 | ~   | 2017 | 2018 | 3 201 | 19 20 | 020 | 2021 | 2022 | 2023 | 2024 | 2025 |
|-------|------|-----|------|------|-------|-------|-----|------|------|------|------|------|
| Code  | W    | ~   | Е    | F    | G     |       | H   | ı    | J    | K    | L    | М    |
| Month | Jan  | Feb | Mar  | Apr  | May   | Jun   | Jul | Aug  | Sep  | Oct  | Nov  | Dec  |
| Code  | 1    | 2   | 3    | 1    | 5     | 6     | 7   | Ω    | Q    | 0    | N    | ר    |



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

| Characteristi  | С               |                                  | Symbol         | Value        | Unit |
|--|-----------------|----------------------------------|----------------|--------------|------|
| Drain-Source Voltage                                   |                 | V <sub>DSS</sub>                 | -20            | V            |      |
| Gate-Source Voltage                                    |                 | V <sub>GSS</sub>                 | ±8             | V            |      |
| Continuous Drain Current (Note 6)                      | Steady<br>State | $T_A = +25$ °C<br>$T_A = +70$ °C | I <sub>D</sub> | -3.6<br>-2.9 | А    |
| Pulsed Drain Current (Note 7)                          |                 | I <sub>DM</sub>                  | -24            | А            |      |
| Maximum Continuous Body Diode Forward Current (Note 6) |                 |                                  | Is             | -1.2         | A    |
| Pulsed Body Diode Forward Current (Note                | e 7)            |                                  | Ism            | -24          | A    |

## **Thermal Characteristics**

| Characteristic  | Symbol                            | Value       | Unit |
|---|-----------------------------------|-------------|------|
| Power Dissipation (Note 6)                                      | $P_{D}$                           | 0.81        | W    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C | $R_{\theta JA}$                   | 153.5       | °C/W |
| Operating and Storage Temperature Range                         | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

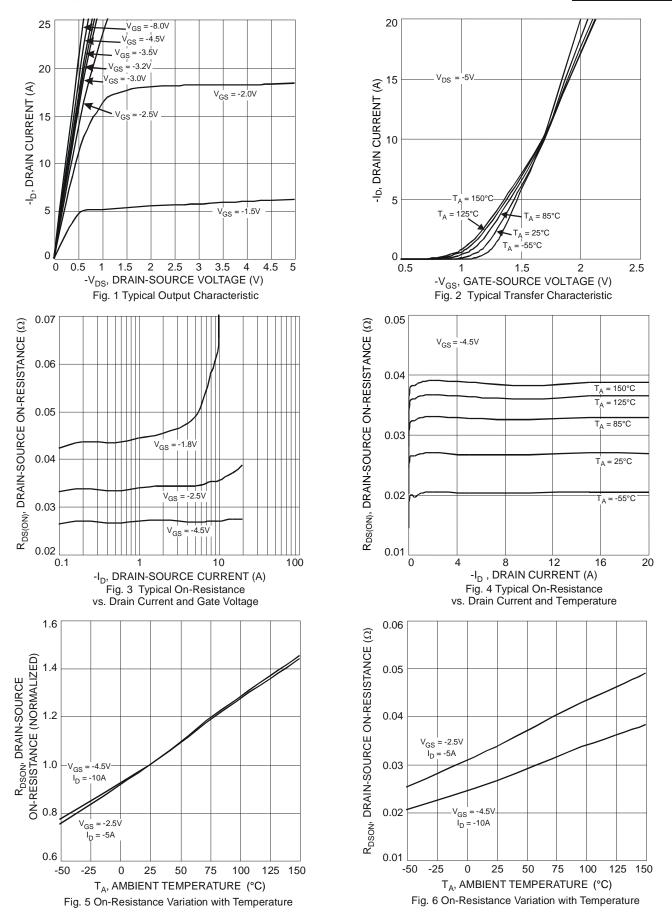
# **Electrical Characteristics** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

| Characteristic   | Symbol              | Min  | Тур            | Max            | Unit | Test Condition                               |  |
|--|---------------------|------|----------------|----------------|------|--|--|
| OFF CHARACTERISTICS (Note 8)                           |                     |      |                |                |      |  |  |
| Drain-Source Breakdown Voltage                         |                     | -20  | _              | _              | V    | $V_{GS} = 0V, I_D = -250\mu A$               |  |
| Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C | I <sub>DSS</sub>    | _    | _              | -1.0           | μA   | V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V |  |
| Gate-Source Leakage                                    | I <sub>GSS</sub>    | _    | _              | ±10            | μΑ   | $V_{GS} = \pm 8V$ , $V_{DS} = 0V$            |  |
| ON CHARACTERISTICS (Note 8)                            |                     |      |                |                |      |  |  |
| Gate Threshold Voltage                                 | V <sub>GS(TH)</sub> | -0.4 | -0.7           | -1.0           | V    | $V_{DS} = V_{GS}, I_{D} = -250\mu A$         |  |
|  |                     |      | 23<br>30<br>41 | 35<br>45<br>62 |      | $V_{GS} = -4.5V, I_D = -4.0A$                |  |
| Static Drain-Source On-Resistance                      | R <sub>DS(ON)</sub> | _    |                |                | mΩ   | $V_{GS} = -2.5V, I_D = -4.0A$                |  |
|  |                     |      |                |                |      | $V_{GS} = -1.8V, I_D = -2.0A$                |  |
| Forward Transfer Admittance                            | Y <sub>fs</sub>     | _    | 14             | _              | S    | $V_{DS} = -5V, I_{D} = -4A$                  |  |
| Diode Forward Voltage                                  | $V_{SD}$            | _    | -0.7           | -1.0           | V    | $V_{GS} = 0V, I_{S} = -1A$                   |  |
| DYNAMIC CHARACTERISTICS (Note 9)                       |                     |      |                |                |      |  |  |
| Input Capacitance                                      | C <sub>iss</sub>    | -    | 1,610          | _              | pF   |  |  |
| Output Capacitance                                     | Coss                | _    | 157            | _              | pF   | $V_{DS} = -10V, V_{GS} = 0V$<br>- f = 1.0MHz |  |
| Reverse Transfer Capacitance                           | Crss                | _    | 145            | _              | pF   | 1 = 1.0WHZ                                   |  |
| Gate Resistance  | Rg                  | _    | 9.45           | _              | Ω    | $V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$   |  |
| Total Gate Charge                                      | Qg                  | _    | 15.4           | _              | nC   |  |  |
| Gate-Source Charge                                     | Q <sub>gs</sub>     | _    | 2.5            | _              | nC   | $V_{GS} = -4.5V, V_{DS} = -10V,$             |  |
| Gate-Drain Charge                                      | $Q_{gd}$            | _    | 3.3            | _              | nC   | $I_D = -4A$                                  |  |
| Turn-On Delay Time                                     | t <sub>D(ON)</sub>  | _    | 16.8           | _              | ns   |  |  |
| Turn-On Rise Time                                      | t <sub>R</sub>      | _    | 12.4           | _              | ns   | $V_{DS} = -10V, V_{GS} = -4.5V,$             |  |
| Turn-Off Delay Time                                    | t <sub>D(OFF)</sub> |      | 94.1           | _              | ns   | $R_L = 10\Omega, R_g = 6.0\Omega, I_D = -1A$ |  |
| Turn-Off Fall Time                                     | t <sub>F</sub>      | _    | 42.4           | _              | ns   |  |  |

Notes:

- 6. Device mounted on FR-4 PCB with 2oz. Copper and test pulse width t ≦10s.
- 7. Repetitive rating, pulse width limited by junction temperature.
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to product testing.









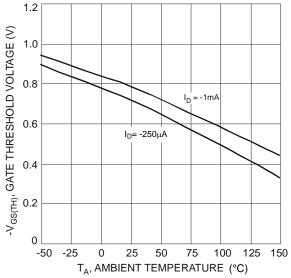
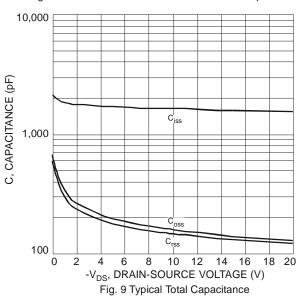
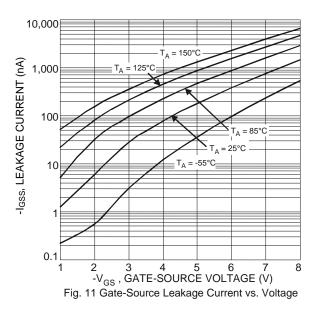
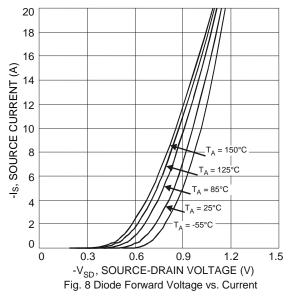
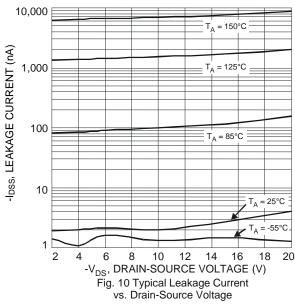


Fig. 7 Gate Threshold Variation vs. Ambient Temperature









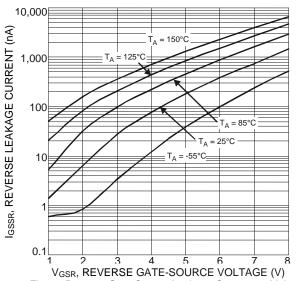
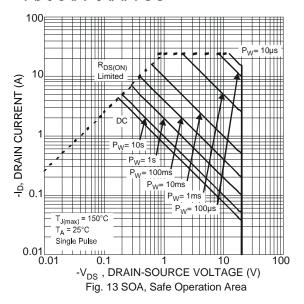


Fig. 12 Reverse Gate-Source Leakage Current vs. Voltage





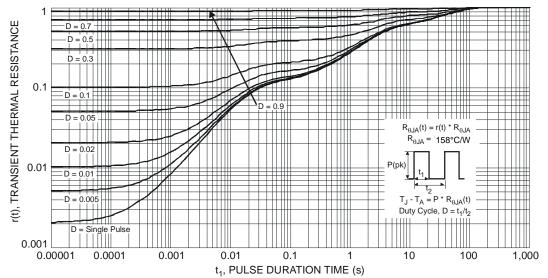


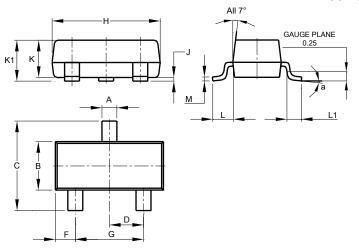
Fig. 14 Transient Thermal Response



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23

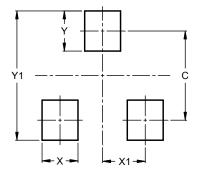


| SOT23                |       |       |       |  |  |  |  |
|----------------------|-------|-------|-------|--|--|--|--|
| Dim                  | Min   | Max   | Тур   |  |  |  |  |
| Α                    | 0.37  | 0.51  | 0.40  |  |  |  |  |
| В                    | 1.20  | 1.40  | 1.30  |  |  |  |  |
| С                    | 2.30  | 2.50  | 2.40  |  |  |  |  |
| D                    | 0.89  | 1.03  | 0.915 |  |  |  |  |
| F                    | 0.45  | 0.60  | 0.535 |  |  |  |  |
| G                    | 1.78  | 2.05  | 1.83  |  |  |  |  |
| Н                    | 2.80  | 3.00  | 2.90  |  |  |  |  |
| 7                    | 0.013 | 0.10  | 0.05  |  |  |  |  |
| K                    | 0.890 | 1.00  | 0.975 |  |  |  |  |
| K1                   | 0.903 | 1.10  | 1.025 |  |  |  |  |
| L                    | 0.45  | 0.61  | 0.55  |  |  |  |  |
| L1                   | 0.25  | 0.55  | 0.40  |  |  |  |  |
| М                    | 0.085 | 0.150 | 0.110 |  |  |  |  |
| а                    | 0°    | 8°    |       |  |  |  |  |
| All Dimensions in mm |       |       |       |  |  |  |  |

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23



| Dimensions | Value (in mm) |
|------------|---------------|
| С          | 2.0           |
| Х          | 0.8           |
| X1         | 1.35          |
| Y          | 0.9           |
| Y1         | 29            |



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